ancement of spin-pumping voltage through the spin-Seebeck ef

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sample set-up sample system: Y₃Fe₅O₁₂ (2.6 μm) / Pt (15 nm) + heater



measuring spin-pumping voltage with applying temperature gradient (spin pumping effect + spin-Seebeck effect)

H dependence of *V* (spin-Seebeck effect)



consistent with inverse spin-Hall effect and spin-seebeck effect model

H dependence of voltage induced by spin pumping



H dependence of voltage induced by spin pumping

without temperature gradient

with temperature gradient ($\Delta T = 16.3K$)



Spin pumping voltage is enhanced !!

H dependence of voltage induced by spin pumping



he amplitude of voltage generated by spin-pumping increas



Temperature gradient dependence of voltage induced by spin pumping



Temperature gradient dependence of voltage induced by spin pumping



Microwave power dependence of voltage induced by spin pumping



 the amplitude of voltage signal is proportional to emission-microwave power Microwave power P(mW)

consistent with ISHE and direct-current spin pumping

model

Conclusion

By using a bilayer film comprising Pt and single crystalline YIG with temperature gradient,

we found that voltage signal induced by spin pumping effect is enhanced due to the spin-Seebeck effect.

